What is Claimed is:

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[c9]

[c1] A method for preventing contamination after plating a metal or an alloy on a surface of a substrate comprising: a) providing a plating solution on the surface of the substrate; b) electroplating or electrolysis plating the metal or alloy on the surface of the substrate; and, c) introducing a stabilizing agent which keeps metal or alloy ions in the plating solution. Method according to claim 1, wherein in said introducing step (c) the stabilizing [c2] agent prevents formation of precipitated salts on the surface of the substrate. [c3] Method according to claim 1, wherein the stabilizing agent comprises an aqueous solution of a complexing agent for the plating metals. [c4] Method according to claim 3, wherein the complexing agent comprises an organic or/inorganic compound. [c5] Method according to claim 3, wherein the complexing agent comprises a mixture of an organic compound and an inorganic compound. Method according to claim \mathcal{B} , wherein the aqueous solution of the complexing [c6] agent for the plating metals comprises Citrate, Acetate, EDTA, or Ammonia. Method according to claim 6, wherein in said introducing step (c) at least one of [c7] the aqueous solutions of the complexing agent is introduced in the following concentrations: Citrate in a preferred concentration/of about 0.5 to about 1.0 mol/kg, Acetate in a preferred concentration of about 0.5 mol/kg, EDTA in a preferred concentration of about 0.2 to about 0.5 mol/kg, and/or Ammonia in a preferred concentration of about 0.1 to about 1.0 mol/kg. Method according to claim 1/wherein the stabilizing agent comprises an acid. [c8]

Method according to claim 8, wherein the acid does not form a low-soluble salt

		with the plated metals.
d.	[c10]	Method according to claim 8, wherein the acid comprises an organic or
		inorganic compound.
	[c11]	Method according to claim 8, wherein the acid comprises a mixture of an
		organic compound and an inorganic compound.
	[c12]	Method according to claim 8, wherein the acid comprises aqueous solutions of
		Hydrochloric Acid, Sulfuric Acid, or Phosphoric Acid.
	[c13]	Method according to claim 12, wherein in said introducing step (c) at least one
		of the aqueous solutions is introduced in the following concentrations:
		Hydrochloric Acid in a preferred concentration of about 0.1 mol/kg,
Į,		Hydrochloric Acid in a preferred concentration of about 0.01 mol/kg,
J		Sulfuric Acid in a preferred concentration of about 0.05 mol/kg, and/or
Hall the lies has the truly and with with with		Phosphoric Acid in a preferred concentration of about 0.1 mol/kg.
	[c14]	Method according to claim 1, wherein the stabilizing agent comprises a mixture
		of an agueous solution of a complexing agent for the plating metals and an
# # T		acid.
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ių.	[c15]	Method according to claim 1, wherein the stabilizing agent is contained in the
The England Control of the Control		plating solution.
	[c16]	Method according to claim 1, wherein the substrate comprises a semiconductor
		wafer.
	[c17]	A solution for preventing contamination after plating a metal or an alloy on a
		surface of a substrate comprising:
		a plating solution; and
		a stabilizing agent which keeps metal or allow ions in the plating solution.
	[c18]	The solution according to claim 17, wherein the stabilizing agent prevents
		formation of precipitated salts on the surface of the substrate.
	[c19]	The solution according to claim 17, wherein the stabilizing agent comprises an

aqueous solution of a complexing agent for the plating metals.

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\ \J-	[c20]	The solution according to claim 19, wherein the complexing agent comprises an
		organic or inorganic compound.
	[c21]	The solution according to claim 19, wherein the complexing agent comprises a
		mixture of an organic compound and an inorganic compound.
	[c22]	The solution according to claim 19, wherein the aqueous solution of the
	[622]	complexing agent for the plating metals comprises Citrate, Acetate, EDTA, or
		Ammonia.
WY.	[c23]	The solution according to claim 22, wherein at least one of the aqueous
The lim the tast than and		solutions of the complexing agent comprises:
		Citrate in a preferred concentration of about 0.5 to about 1.0 mol/kg,
		Acetate in a preferred foncentration of about 0.5 mol/kg,
		EDTA in a preferred concentration of about 0.2 to about 0.5 mol/kg,
		and/or
19		Ammonia in a preferred concentration of about 0.1 to about 1.0 mol/kg.
allen allen il	[c24]	The solution according to claim 17, wherein the stabilizing agent comprises an
€		acid.
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TÚ.	[c25]	The solution according to claim 24, wherein the acid does not form a low-
The Cast of the Control of the Contr		soluble salt with the plated metals.
ļ.	[c26]	The solution according to claim 24, wherein the acid comprises an organic or
		inorganic compound.
	[c27]	The solution according to claim 24, wherein the acid comprises a mixture of an
	[]	organic compound and an inorganic compound.
	[c28]	The solution according to claim 24, wherein the acid comprises aqueous
		solutions of Hydrochloric Acid, Sulfuric Acid, or Phosphoric Acid.
	[c29]	
		The solution according to claim 28, wherein at least one of the aqueous
		solutions of the acid comprises:
		Hydrochloric Acid in a preferred concentration of about 0.1 mol/kg,
		Hydrochloric Acid in a preferred concentration of about 0.01 mol/kg,



 Sulfuric Acid in a preferred concentration of about 0.05 mol/kg, and/or Phosphoric Acid in a preferred concentration of about 0.1 mol/kg.

[c30] The solution according to claim 17, wherein the stabilizing agent comprises a mixture of an aqueous solution of a complexing agent for the plating metals and an acid.

[c31]

[c32]

[c33]

The solution according to claim 17, wherein the stabilizing agent is contained in the plating solution.

The solution according to claim 17, wherein the substrate comprises a semiconductor wafer.

In a method for plating a metal alloy on a surface of a substrate by electrolytic activity using a plating solution on the surface wherein the improvement comprises introducing a stabilizing agent onto the substrate surface in order to keep metal alloy ions in the plating solution.

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